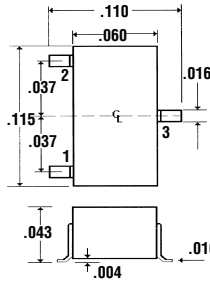
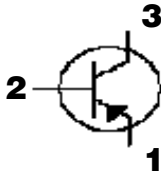
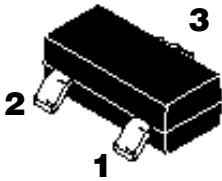




FMBT1015



Maximum Ratings

Ratings	Symbol	Value	Units
Collector - Emitter Voltage	V_{CEO}	-50	V
Collector - Base Voltage	V_{CBO}	-50	V
Emitter - Base Voltage	V_{EBO}	-5.0	V
Collector Current (Continuous)	I_C	-150	mA
Total Device Dissipation FR-5 Board (Note1) $T_A = 25^\circ\text{C}$	P_D	125	mW
Junction and Storage Temperature	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Electrical Characteristics @ 25°C

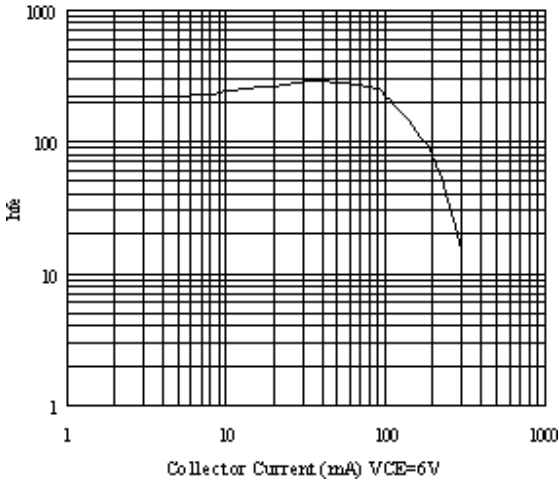
Characteristic	Symbol	Min	Max	Unit
Collector - Emitter Breakdown Voltage ($I_C = -1.0\text{mA}$)	$V_{BR(CEO)}$	-50	---	V
Collector - Base Breakdown Voltage ($I_C = -0.1\text{mA}$)	$V_{BR(CBO)}$	-50	---	V
Emitter - Base Breakdown Voltage ($I_E = -0.01\text{mA}$)	$V_{BR(EBO)}$	-5.0	---	V
Collector Cutoff Current ($V_{CB} = -50\text{V}$)	I_{CBO}	---	-0.1	μA
Emitter Cutoff Current ($V_{EB} = -5.0\text{V}$)	I_{EBO}	---	-0.1	μA
DC Current Gain ($I_C = -2.0\text{ mA}, V_{CE} = -6.0\text{ V}$)* ($I_C = -150\text{ mA}, V_{CE} = -6.0\text{ V}$)	H_{FE}	120 25	600 ---	---
Collector - Emitter Saturation Voltage ($I_C = -100\text{ mA}, I_B = -10\text{ mA}$)	$V_{CE(sat)}$	---	-0.3	Vdc
Base - Emitter Saturation Voltage ($I_C = -100\text{ mA}, I_B = -10\text{ mA}$)	$V_{BE(sat)}$	---	-1.1	Vdc
Current - Gain - Bandwidth Product ($I_C = -1.0\text{ mA}, V_{CE} = -10\text{ V}, f = 100\text{ MHz}$)	f_T	80	---	MHz
Output Capacitance ($V_{CB} = -10\text{ V}, f = 1.0\text{ MHz}$)	C_{ob}	---	7.0	pF

* Classification of h_{FE}

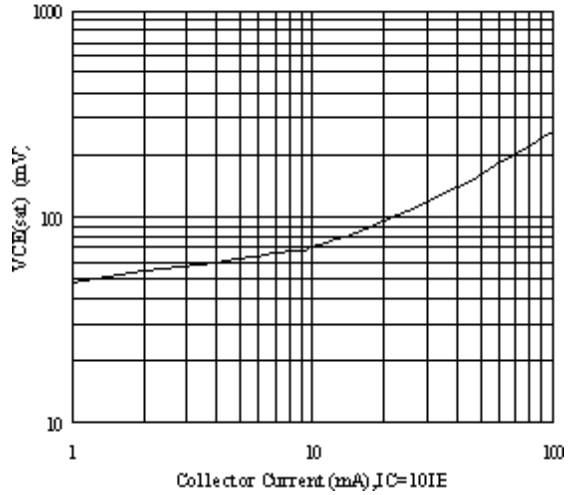
Rank	A4Y	A4G	A4B
Range	120-240	200-400	350-600

FMBT1015 PNP Epitaxial Planar Transistor

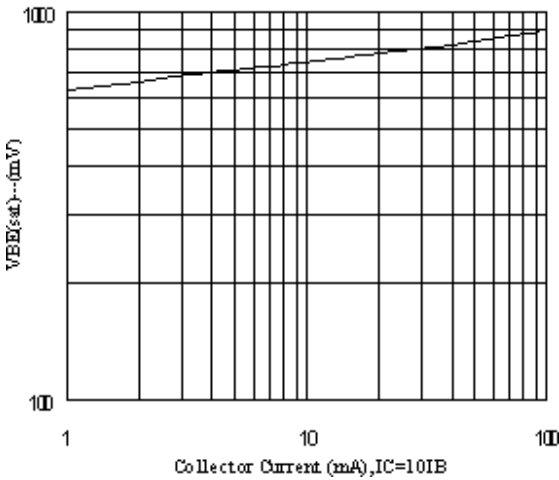
DC CURRENT GAIN VS. COLLECTOR CURRENT



COLLECTOR-EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT



BASE-EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT



VBE(ON) VS. IC

